

MOSFET

600V CoolMOS™ SJ S7 Power Device

IPT60R040S7 enables the best price performance for low frequency switching applications. CoolMOS™ S7 boasts the lowest $R_{DS(on)}$ values for a HV SJ MOSFET, with distinctive increase of energy efficiency.

CoolMOS™ S7 is optimized for “static switching” and high current applications. It is an ideal fit for solid state relay and circuit breaker designs as well as for line rectification in SMPS and inverter topologies.

Features

- CoolMOS™ S7 technology enables $22\text{m}\Omega$ $R_{DS(on)}$ in the smallest footprint
- Optimized price performance in low frequency switching applications
- High pulse current capability
- Kelvin Source pin improves switching performance at high current
- TOLL package is MSL1 compliant, total Pb-free, has easy visual inspection leads

Benefits

- Minimized conduction losses (eliminate / reduce heat sink)
- Increased system performance
- More compact and easier design
- Lower BOM or/and TCO over prolonged life time

Compared to electromechanical devices:

- Faster switching times
- More reliability and longer system life time
- Shock & Vibration resistance
- No contact arcing, bouncing or degradation over life time

Potential applications

- Solid state relays and circuit breakers
- Line rectification in high power/performance applications e.g. Computing, Telecom, UPS and Solar

Product validation

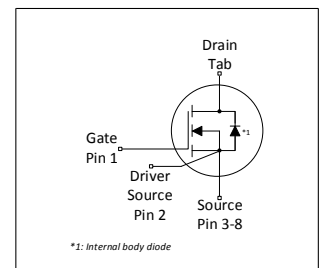
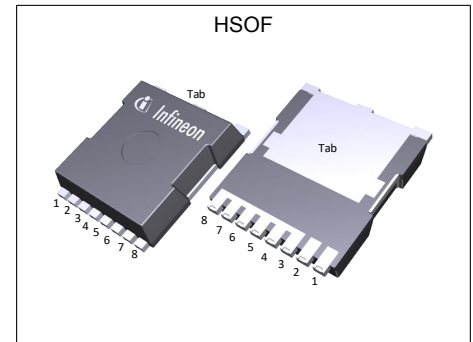
Fully qualified according to JEDEC for Industrial Applications

Please note: For paralleling 4pin MOSFET devices the placement of the gate resistor is generally recommended to be on the Driver Source instead of the Gate.

Table 1 Key Performance Parameters

Parameter	Value	Unit
$R_{DS(on),max}$	40	$\text{m}\Omega$
$Q_{g,typ}$	83	nC
V_{SD}	0.82	V
Pulsed I_{SD}, I_{DS}	207	A

Type / Ordering Code	Package	Marking	Related Links
IPT60R040S7	PG-HSOF-8	60R040S7	see Appendix A



RoHS

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1 Maximum ratings

at $T_j = 25^\circ\text{C}$, unless otherwise specified

Table 2 Maximum ratings

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain current rating	I_D	-	-	13	A	$T_C=140^\circ\text{C}$ Current is limited by $T_{j\max} = 150^\circ\text{C}$; Lower case temp does increase current capability
Pulsed drain current ¹⁾	$I_{D,\text{pulse}}$	-	-	207	A	$T_C=25^\circ\text{C}$
Avalanche energy, single pulse	E_{AS}	-	-	159	mJ	$I_D=2.8\text{A}$; $V_{DD}=50\text{V}$; see table 10
Avalanche current, single pulse	I_{AS}	-	-	2.8	A	-
MOSFET dv/dt ruggedness ²⁾	dv/dt	-	-	20	V/ns	$V_{DS}= 0\text{V to }300\text{V}$
Gate source voltage (static)	V_{GS}	-20	-	20	V	static
Gate source voltage (dynamic)	V_{GS}	-30	-	30	V	AC ($f>1\text{ Hz}$)
Power dissipation	P_{tot}	-	-	245	W	$T_C=25^\circ\text{C}$
Storage temperature	T_{stg}	-55	-	150	$^\circ\text{C}$	-
Operating junction temperature	T_j	-55	-	150	$^\circ\text{C}$	-
Mounting torque	-	-	-	n.a.	Ncm	-
Diode forward current rating	I_S	-	-	13	A	$T_C=140^\circ\text{C}$ Current is limited by $T_{j\max} = 150^\circ\text{C}$; Lower case temp does increase current capability
Diode pulse current ¹⁾	$I_{S,\text{pulse}}$	-	-	207	A	$T_C=25^\circ\text{C}$
Reverse diode dv/dt ³⁾	dv/dt	-	-	5	V/ns	$V_{DS}=0\text{ to }300\text{V}$, $I_{SD}\leq 13\text{A}$, $T_j=25^\circ\text{C}$ see table 8
Maximum diode commutation speed	di/dt	-	-	1000	A/ μs	$V_{DS}=0\text{ to }300\text{V}$, $I_{SD}\leq 13\text{A}$, $T_j=25^\circ\text{C}$ see table 8
Insulation withstand voltage	V_{ISO}	-	-	n.a.	V	V_{rms} , $T_C=25^\circ\text{C}$, $t=1\text{min}$

¹⁾ Pulse width t_p limited by $T_{j\max}$

²⁾ The dv/dt has to be limited by appropriate gate resistor

³⁾ Identical low side and high side switch

2 Thermal characteristics

Table 3 Thermal characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	R_{thJC}	-	-	0.51	°C/W	-
Thermal resistance, junction - ambient	R_{thJA}	-	-	62	°C/W	device on PCB, minimal footprint
Thermal resistance, junction - ambient for SMD version	R_{thJA}	-	35	45	°C/W	Device on 40mm*40mm*1.5mm epoxy PCB FR4 with 6cm ² (one layer, 70µm thickness) copper area for drain connection and cooling. PCB is vertical without air stream cooling.
Soldering temperature, wave- & reflow soldering allowed	T_{sold}	-	-	260	°C	reflow MSL1

3 Electrical characteristics

at $T_j=25^\circ\text{C}$, unless otherwise specified

Table 4 Static characteristics

For applications with applied blocking voltage >70% of the specified blocking voltage, it is required that the customer evaluates the impact of cosmic radiation effect in early design phase and contacts the Infineon sales office for the necessary technical support by Infineon

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	600	-	-	V	$V_{GS}=0V, I_D=1mA$
Gate threshold voltage	$V_{(GS)th}$	3.5	4.0	4.5	V	$V_{DS}=V_{GS}, I_D=0.79mA$
Zero gate voltage drain current	I_{DSS}	-	-	2	μA	$V_{DS}=600V, V_{GS}=0V, T_j=25^\circ C$ $V_{DS}=600V, V_{GS}=0V, T_j=150^\circ C$
Gate-source leakage current	I_{GSS}	-	-	100	nA	$V_{GS}=20V, V_{DS}=0V$
Drain-source on-state resistance	$R_{DS(on)}$	-	0.036	0.040	Ω	$V_{GS}=12V, I_D=13A, T_j=25^\circ C$ $V_{GS}=12V, I_D=13A, T_j=150^\circ C$
Gate resistance	R_G	-	0.80	-	Ω	$f=1MHz, \text{open drain}$

Table 5 Dynamic characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input capacitance	C_{iss}	-	3127	-	pF	$V_{GS}=0V, V_{DS}=300V, f=250kHz$
Output capacitance	C_{oss}	-	50	-	pF	$V_{GS}=0V, V_{DS}=300V, f=250kHz$
Effective output capacitance, energy related ¹⁾	$C_{o(er)}$	-	168	-	pF	$V_{GS}=0V, V_{DS}=0 \text{ to } 300V$
Effective output capacitance, time related ²⁾	$C_{o(tr)}$	-	1476	-	pF	$I_D=\text{constant}, V_{GS}=0V, V_{DS}=0 \text{ to } 300V$
Output charge	Q_{oss}	-	443	-	nC	$V_{GS}=0V, V_{DS}=0 \text{ to } 300V$
Turn-on delay time	$t_{d(on)}$	-	23	-	ns	$V_{DD}=300V, V_{GS}=13V, I_D=13A, R_G=8\Omega; \text{ see table 9}$
Rise time	t_r	-	5	-	ns	$V_{DD}=300V, V_{GS}=13V, I_D=13A, R_G=8\Omega; \text{ see table 9}$
Turn-off delay time	$t_{d(off)}$	-	120	-	ns	$V_{DD}=300V, V_{GS}=13V, I_D=13A, R_G=8\Omega; \text{ see table 9}$
Fall time	t_f	-	9	-	ns	$V_{DD}=300V, V_{GS}=13V, I_D=13A, R_G=8\Omega; \text{ see table 9}$

Table 6 Gate charge characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gate to source charge	Q_{gs}	-	17	-	nC	$V_{DD}=300V, I_D=13A, V_{GS}=0 \text{ to } 12V$
Gate to drain charge	Q_{gd}	-	28	-	nC	$V_{DD}=300V, I_D=13A, V_{GS}=0 \text{ to } 12V$
Gate charge total	Q_g	-	83	-	nC	$V_{DD}=300V, I_D=13A, V_{GS}=0 \text{ to } 12V$
Gate plateau voltage	$V_{plateau}$	-	5.4	-	V	$V_{DD}=300V, I_D=13A, V_{GS}=0 \text{ to } 12V$

¹⁾ $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 300V

²⁾ $C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 300V

Table 7 Reverse diode characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Diode forward voltage	V_{SD}	-	0.82	-	V	$V_{GS}=0V, I_F=13A, T_j=25^\circ C$
Reverse recovery time	t_{rr}	-	360	-	ns	$V_R=300V, I_F=13A, di_F/dt=100A/\mu s$; see table 8
Reverse recovery charge	Q_{rr}	-	5.5	-	μC	$V_R=300V, I_F=13A, di_F/dt=100A/\mu s$; see table 8
Peak reverse recovery current	I_{rrm}	-	32	-	A	$V_R=300V, I_F=13A, di_F/dt=100A/\mu s$; see table 8

4 Electrical characteristics diagrams

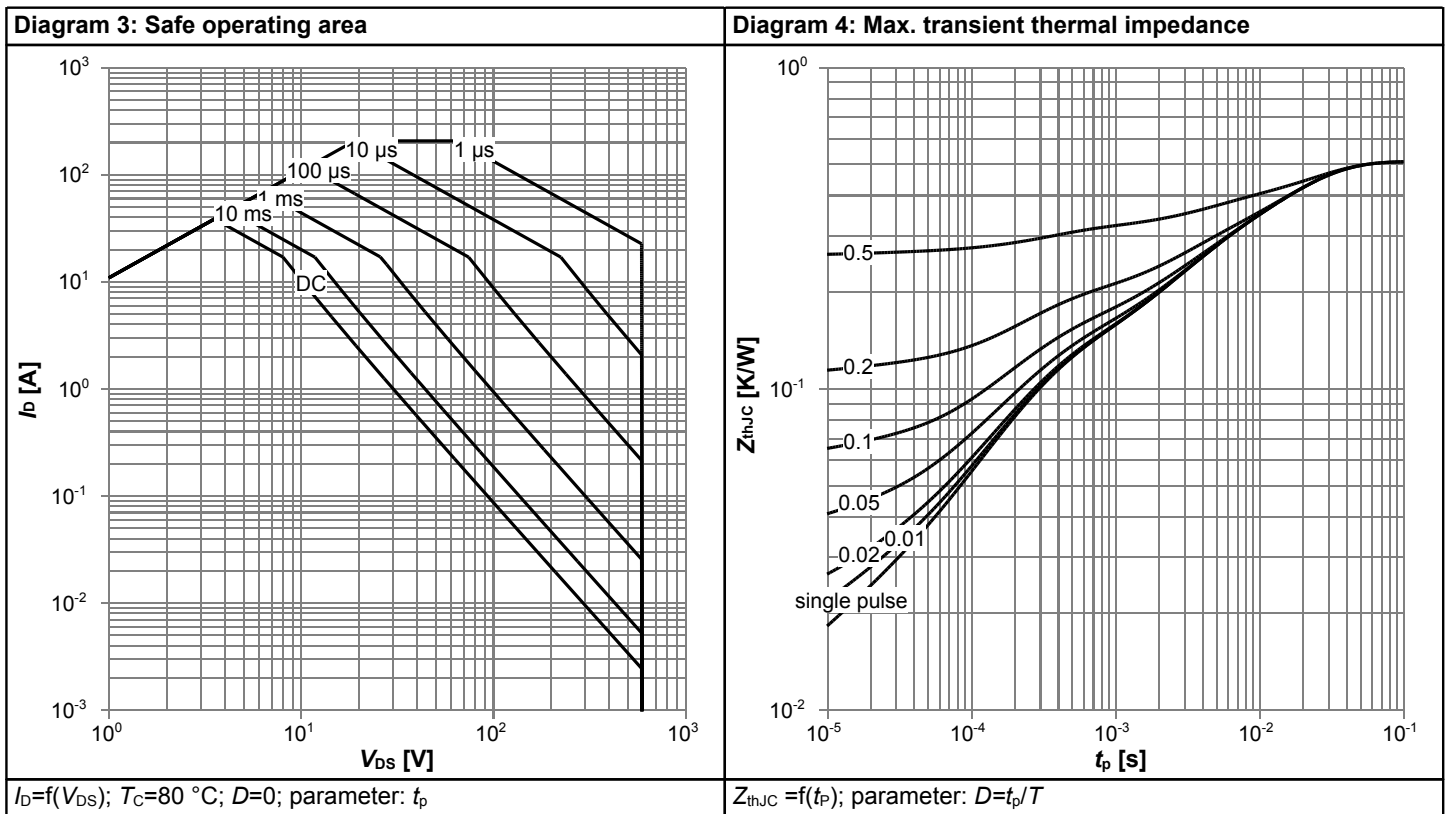
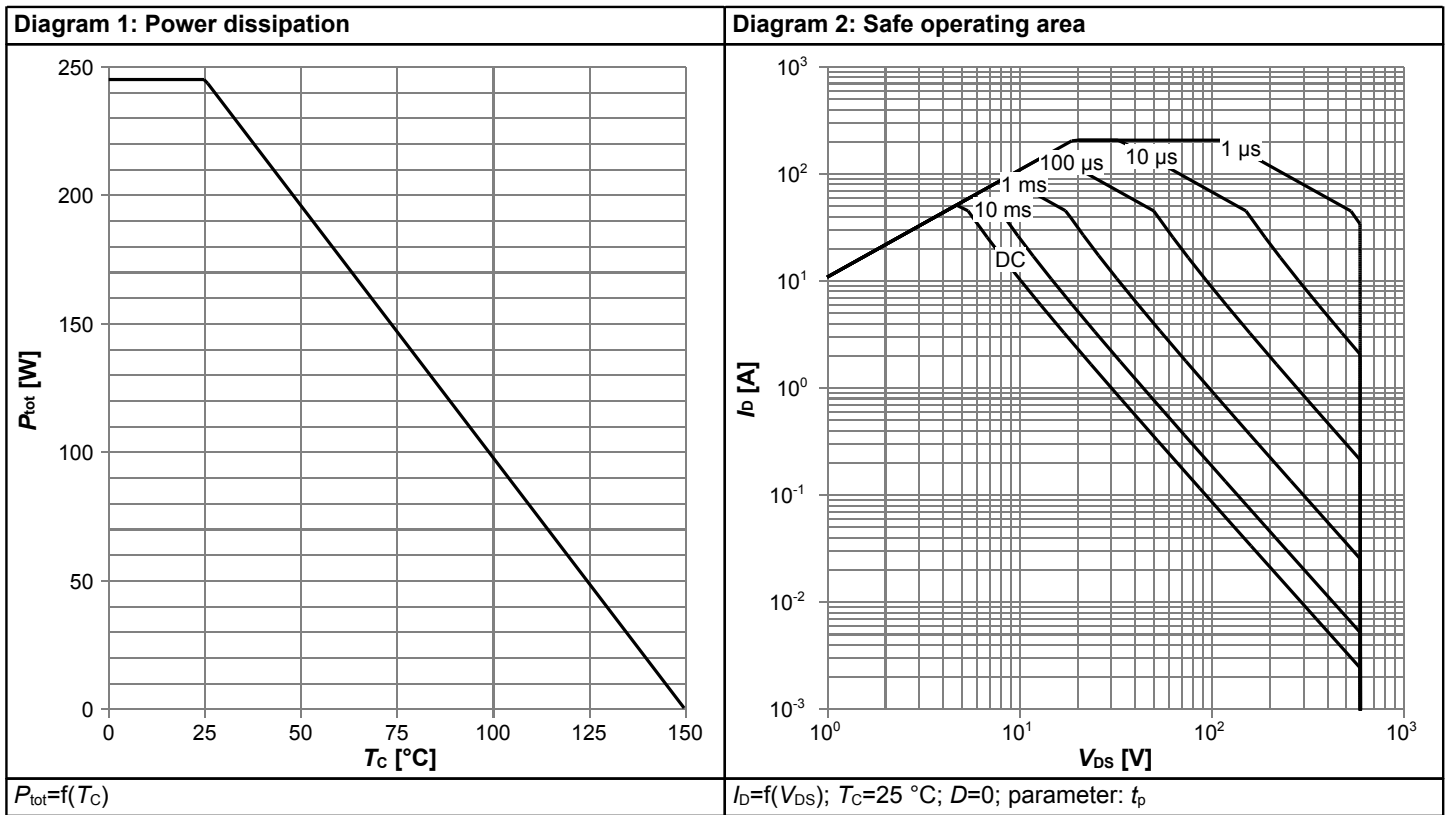
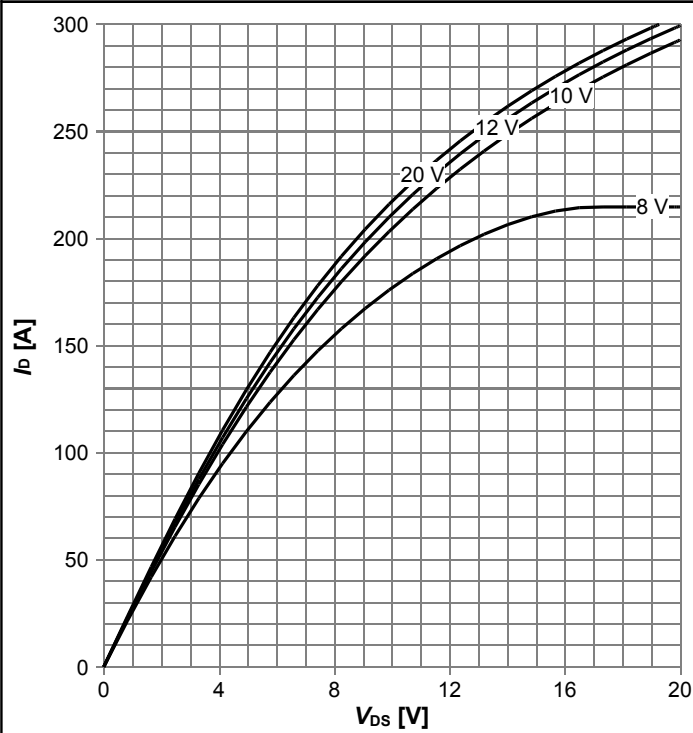
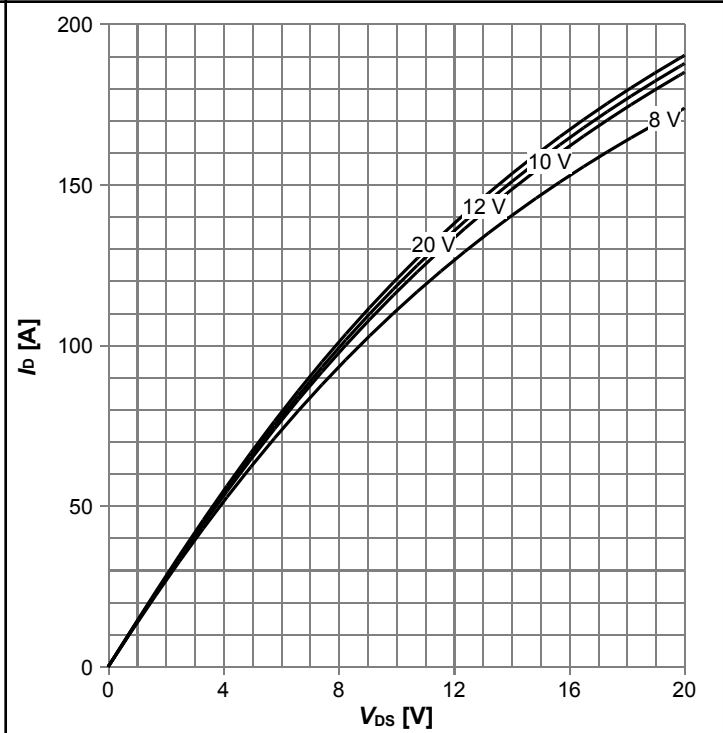


Diagram 5: Typ. output characteristics



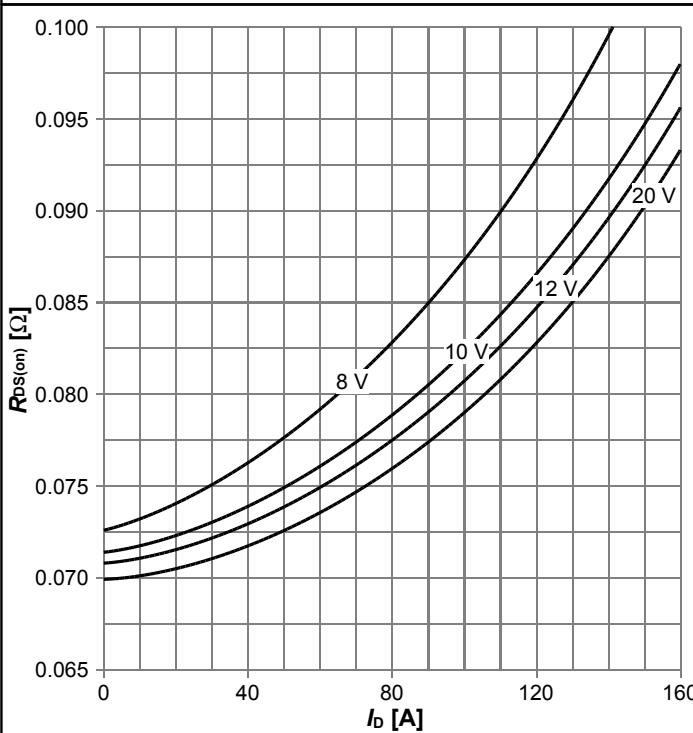
$I_D = f(V_{DS})$; $T_j = 25\text{ °C}$; parameter: V_{GS}

Diagram 6: Typ. output characteristics



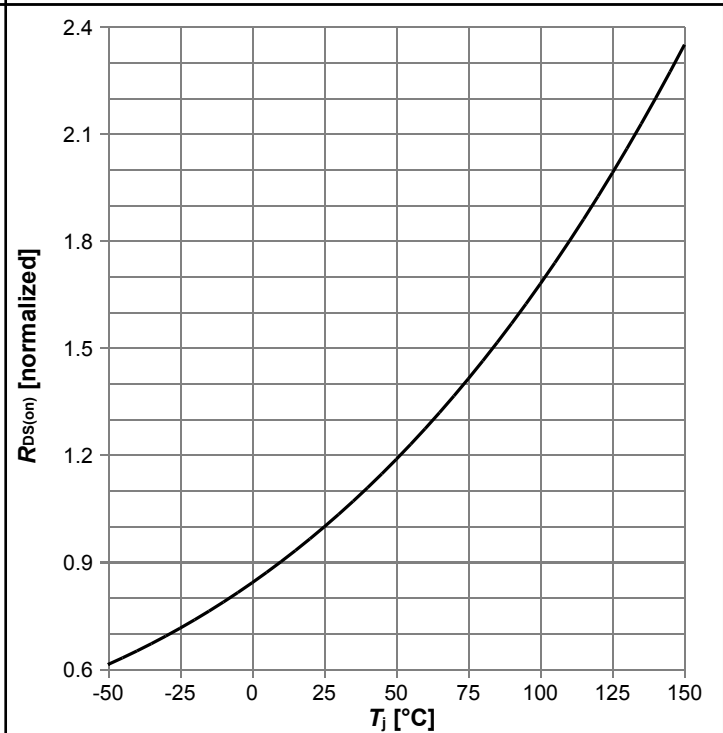
$I_D = f(V_{DS})$; $T_j = 125\text{ °C}$; parameter: V_{GS}

Diagram 7: Typ. drain-source on-state resistance



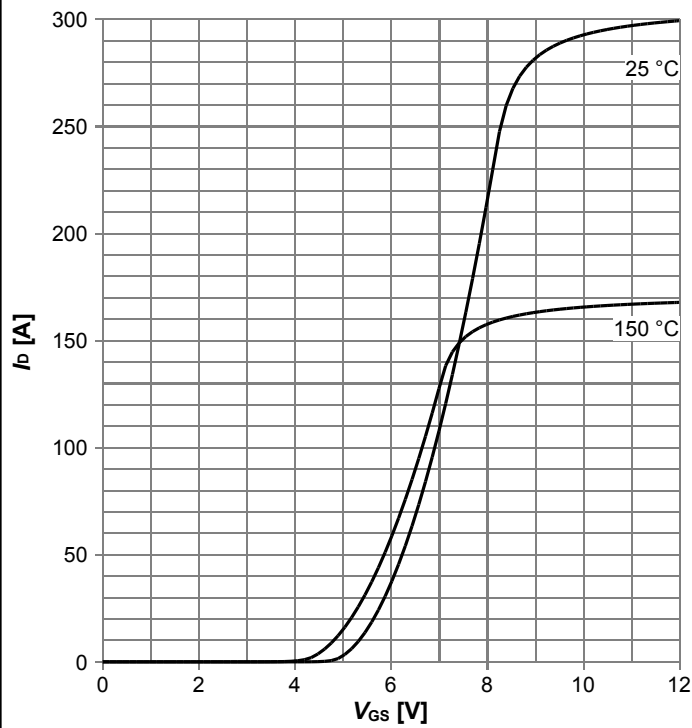
$R_{DS(on)} = f(I_D)$; $T_j = 125\text{ °C}$; parameter: V_{GS}

Diagram 8: Drain-source on-state resistance



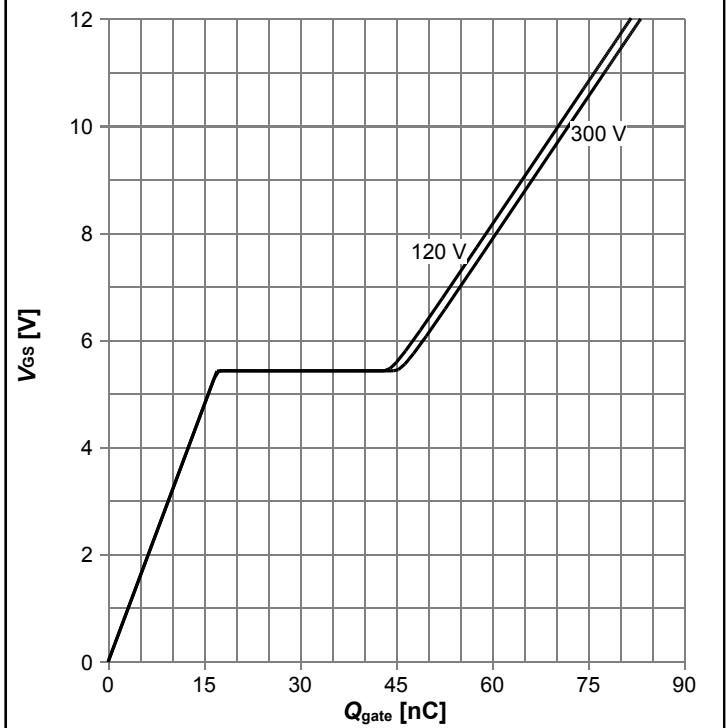
$R_{DS(on)} = f(T_j)$; $I_D = 13.0\text{ A}$; $V_{GS} = 12\text{ V}$

Diagram 9: Typ. transfer characteristics



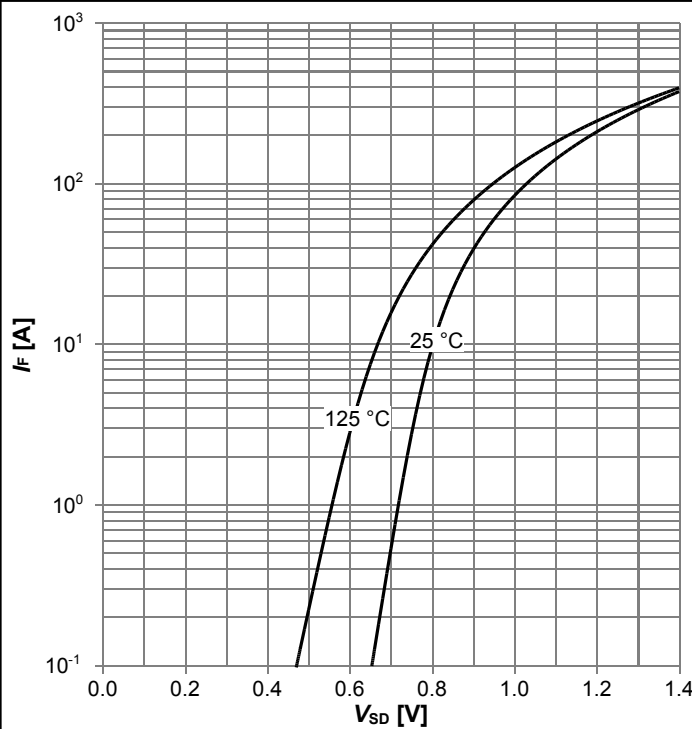
$I_D = f(V_{GS})$; $V_{DS} = 20V$; parameter: T_j

Diagram 10: Typ. gate charge



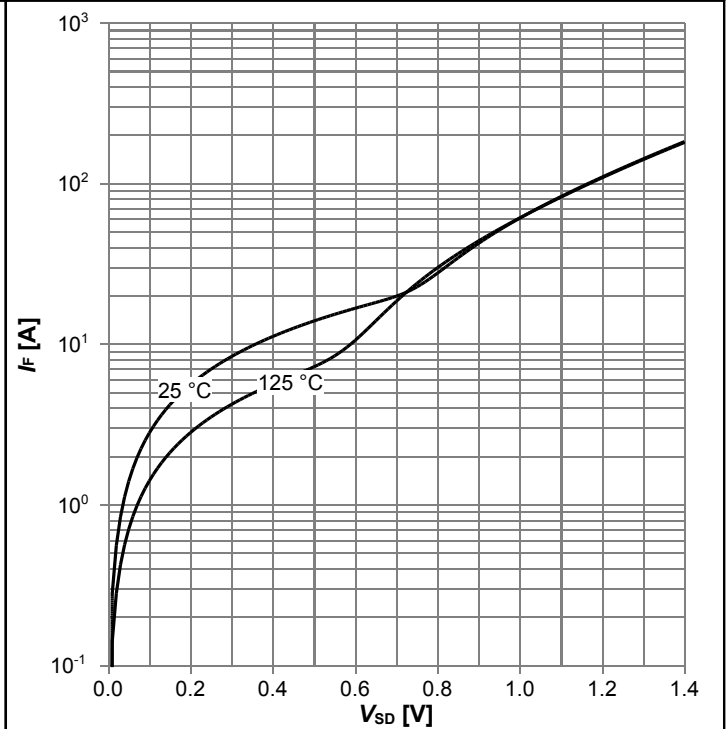
$V_{GS} = f(Q_{gate})$; $I_D = 13.0 A$ pulsed; parameter: V_{DD}

Diagram 11: Forward characteristics of reverse diode



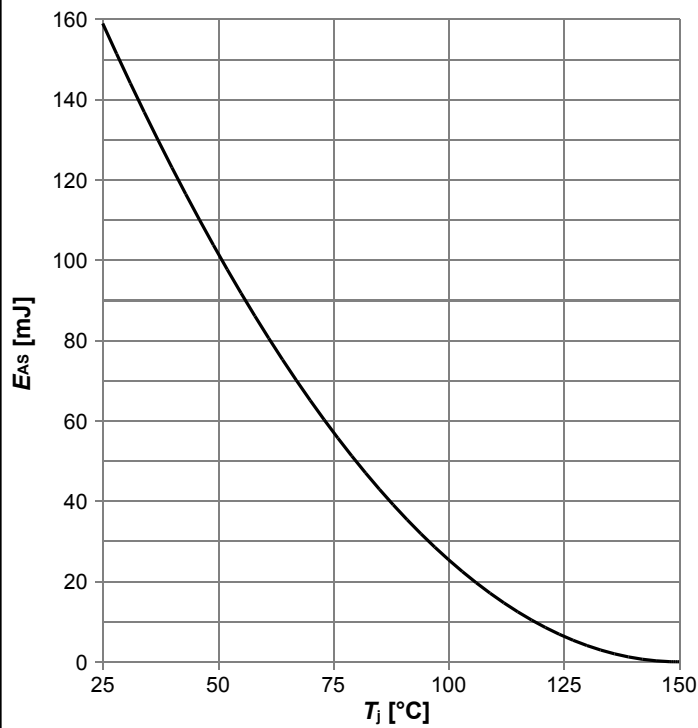
$I_F = f(V_{SD})$; $V_{GS} = 0 V$; parameter: T_j

Diagram 12: Forward characteristics of reverse diode



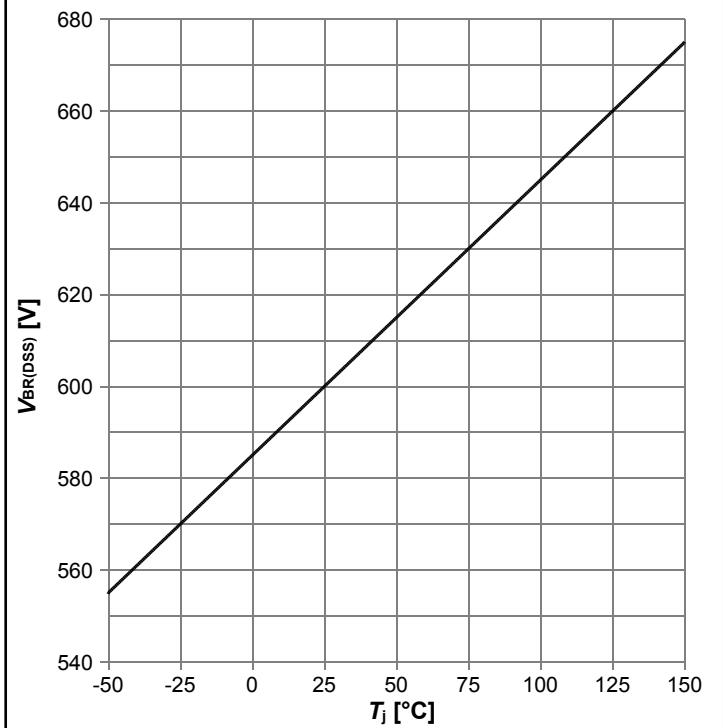
$I_F = f(V_{SD})$; $V_{GS} = 12 V$; parameter: T_j

Diagram 13: Avalanche energy



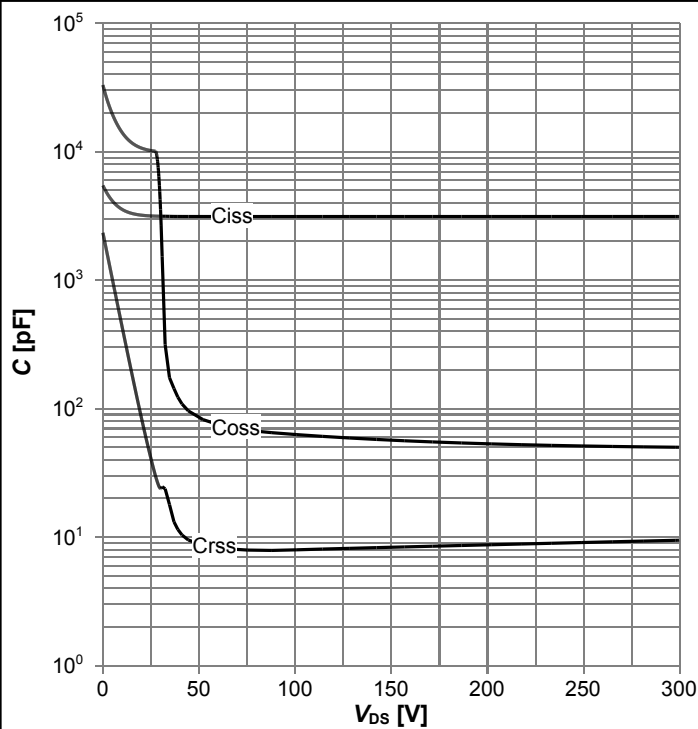
$E_{AS}=f(T_j)$; $I_D=2.8$ A; $V_{DD}=50$ V

Diagram 14: Drain-source breakdown voltage



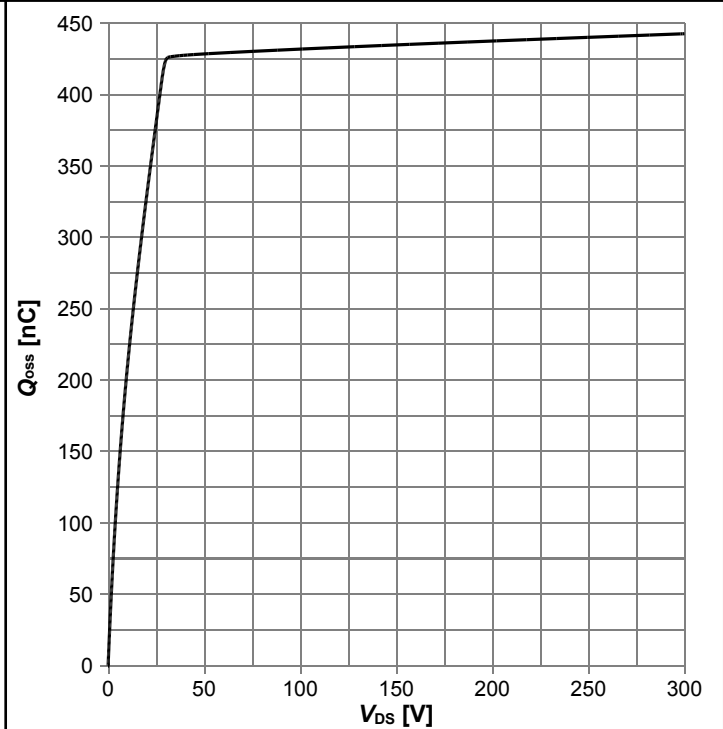
$V_{BR(DSS)}=f(T_j)$; $I_D=1$ mA

Diagram 15: Typ. capacitances



$C=f(V_{DS})$; $V_{GS}=0$ V; $f=250$ kHz

Diagram 17: Typ. Qoss output charge



$Q_{oss}=f(V_{DS})$; $V_{GS}=0$ V

5 Test Circuits

Table 8 Diode characteristics

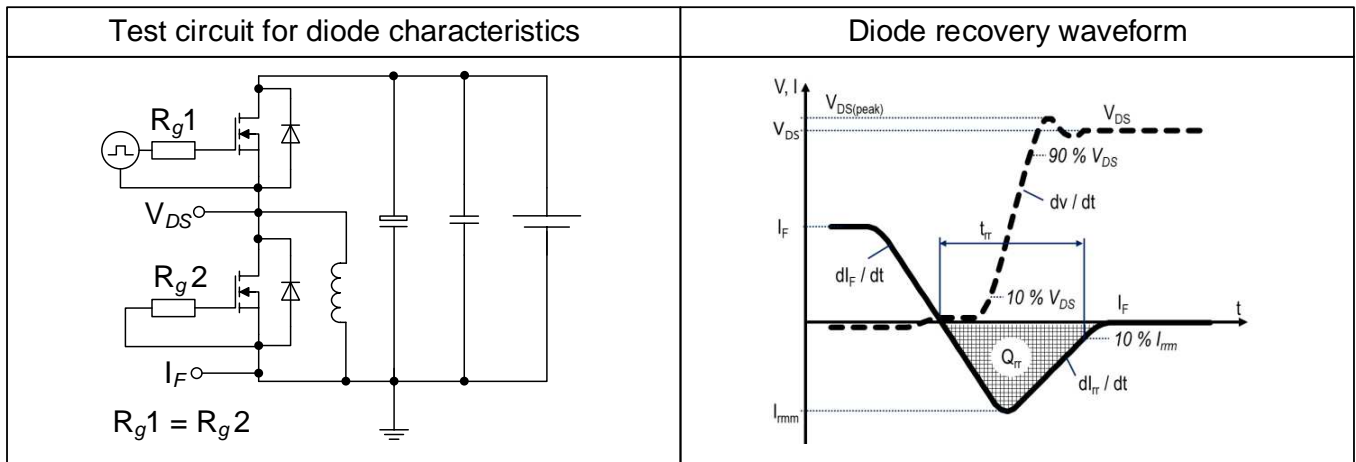


Table 9 Switching times (ss)



Table 10 Unclamped inductive load (ss)



6 Package Outlines



Figure 1 Outline PG-HSOF-8, dimensions in mm/inches

7 Appendix A

Table 11 Related Links

- IFX CoolMOS S7 Webpage: www.infineon.com
- IFX CoolMOS S7 application note: www.infineon.com
- IFX CoolMOS S7 simulation model: www.infineon.com
- IFX Design tools: www.infineon.com

Revision History

IPT60R040S7

Revision: 2021-10-25, Rev. 2.1

Previous Revision

Revision	Date	Subjects (major changes since last revision)
2.0	2019-05-07	Release of final version
2.1	2021-10-25	Change of wording regarding breakdown voltage / cosmic ray

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